

# Atomic Force Microscopy (AFM) analysis service

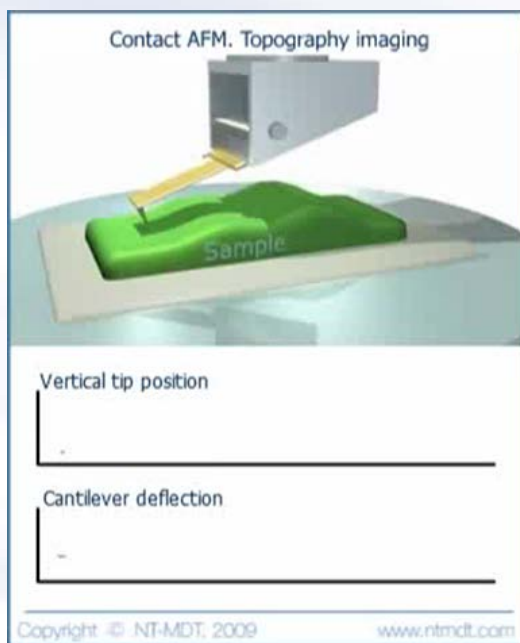
Atomic Force Microscopy (AFM) is used to narrow down the failure location of a via or transistor in an larger area, found after EMMI/OBIRCH/LIT failure localisation analysis.

Further failure analysis step is delayering or FIB cross-sectioning



## PARK NX10 FEATURES:

- Auto engage by Slide-to-Connect SLD head
- Expansion slot for advanced SPM modes and options
- High speed 24-bit digital electronics
- Direct on-axis high powered optics with integrated LED illumination
- Accessible Sample Holder



## STAGE & SCANNER:

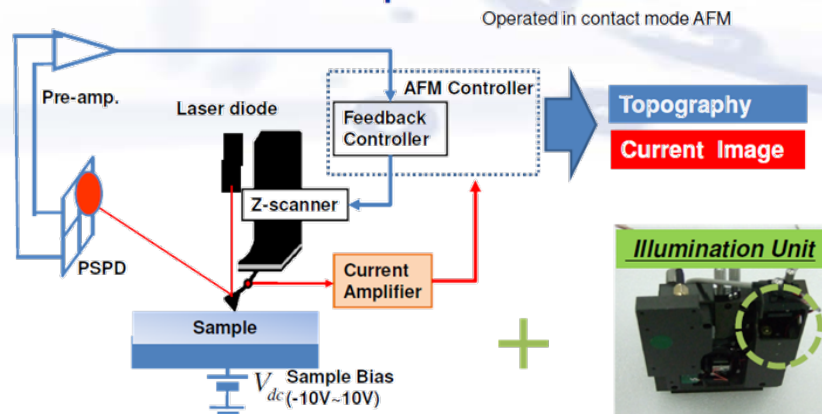
Scanner:

- 100  $\mu\text{m}$  x 100  $\mu\text{m}$  XY Scanner (normal 50  $\mu\text{m}$  x 50  $\mu\text{m}$ )
- Max Resolution: 0.05 nm
- 15  $\mu\text{m}$  Scan Range
- Pre-mounted tips

Electrical Properties:

- Conductive AFM mode
- I-V Spectroscopy

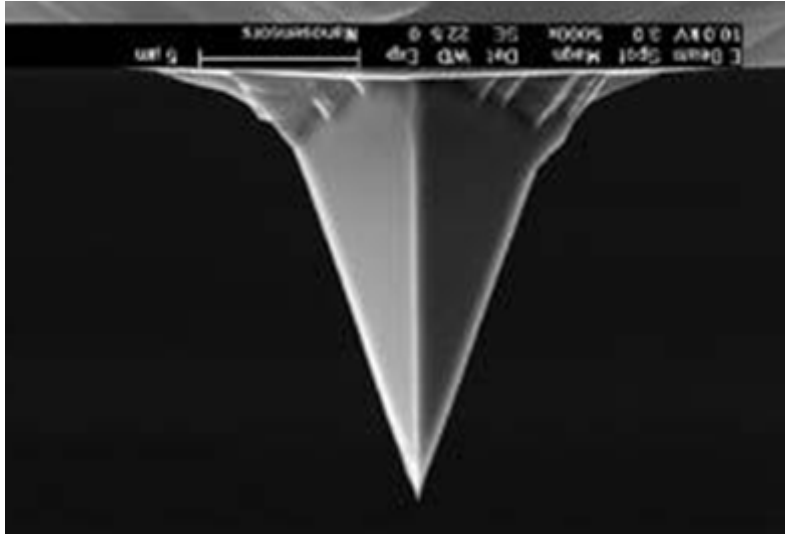
## Conductive AFM Setup



## SCANNING MODES:

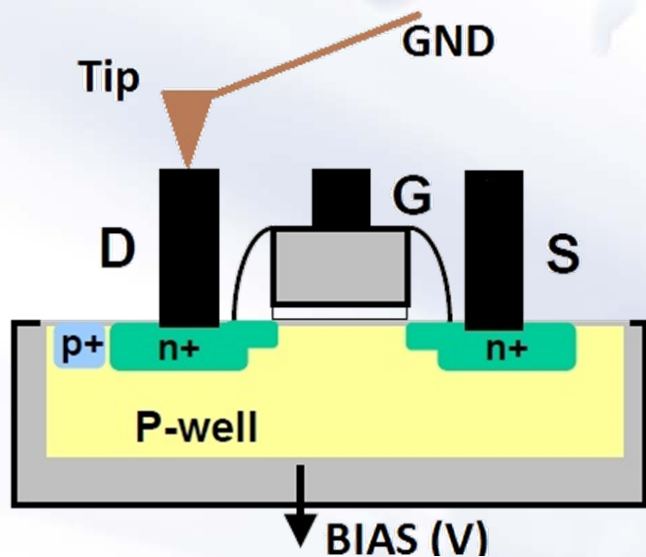
- True Non-Contact AFM
- Basic Contact AFM
- Intermitted (tapping) AFM

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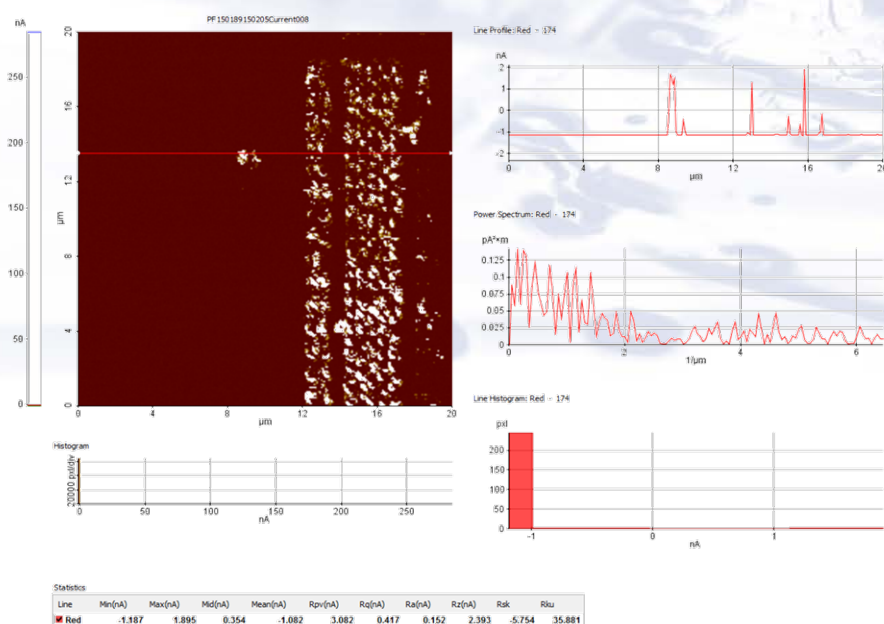
## MEASUREMENT MODES:

- Surface Morphology \*
  - Conductive AFM \*
  - Electrostatic Force Microscopy (EFM) \*
  - Surface potential Microscopy, kelvin Probe (SKPM)
  - Force Modulation Microscopy (FMM) \*
  - Lateral Force Microscopy (LFM) \*
  - Magnetic Force Microscopy (MFM)
  - Scanning Tunneling Microscopy (STM) \*
  - Fluid AFM
- \* = Available at Maser



## AFM APPLICATIONS:

- Identification of a leakage of a via or transistor
- Pinpoint of location with a very high accuracy after polishing
- Local I-V curve measurement while leaving the tips on a certain spot/contact
- Failure confirmation by further delayering or FIB cross-sectioning



## APPLICATION EXAMPLES:

- Gate Oxide breakdown (SEM inspection after poly etch)
- Open plugs (via's or transistor plugs)
- Molten plugs (via's or transistor plugs)
- Surface roughness measurement